

Supplementary

# Thickness-Dependence Electrical Characterization of the One-Dimensional van der Waals TaSe<sub>3</sub> Crystal

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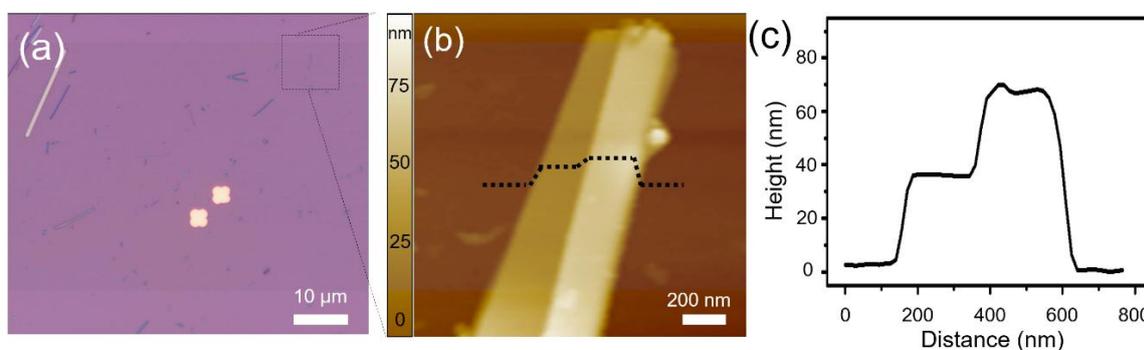
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**Figure S1.** (a) OM and (b) AFM image of exfoliated TaSe<sub>3</sub> flakes on 300 nm SiO<sub>2</sub>/Si substrate. (c) Line profile of the corresponding TaSe<sub>3</sub> flake, as marked in (b).



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